# Recombination of ortho and para $H_3^+$ ions with electrons at low temperatures using flowing afterglow technique

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# 1. Introduction

 $H_3^+$  – the simplest polyatomic ion – plays a pivotal role in the chemical evolution of interstellar clouds [1]. Its recombination with electrons is of interest for modeling hydrogen containing plasmas and has been studied experimentally and theoretically for over 60 years [2].

The quantum mechanical calculations [3] predict that at low temperatures the two spin isomers of  $H_3^+$ ion (ortho and para) have different recombination rates. A small enhancement of para  $H_3^+$ recombination rate was found in storage ion ring experiments [4,5] but the ions stored in the ring were probably not rotationally cold [6]. Theoretical predictions are supported by stationary afterglow experiments with in situ determined populations of recombining ions [7].

As in stationary afterglow setup the reactants are subject to discharge, the presence of excited molecules in afterglow plasma cannot be completely ruled out. Therefore, we decided to study the state specific recombination of  $H_3^+$  ions using Cryogenic Flowing Afterglow apparatus (Cryo-FALP II) where the discharge and the formation of  $H_3^+$  dominated plasma are spatially separated.

## 2. Experiment

The main diagnostic tool used in this study was apparatus **Crvo-FALP** Π [8], where the recombination rate coefficients are evaluated from the time decay of electron number density and the gas temperature can be varied in the range of 40 -300 K. The actual ratio between para and ortho  $H_3^+$ ions was changed by using either normal H<sub>2</sub> (75 % ortho H<sub>2</sub>, 25 % para H<sub>2</sub>) or para enriched H<sub>2</sub> (more than 99% of para  $H_2$ ) as a precursor gas to form  $H_3^+$ ions. The populations of the different rotational states of  $H_3^+$  were monitored using our Stationary Afterglow with Cavity Ring Down Spectrometer setup [7] at similar conditions that were used during the recombination rate coefficient measurements in Cryo-FALP II. Examples of measured absorption line profiles are shown in Fig. 1.

### 3. Results

The recombination rate coefficients measured at 80 K for ortho  $H_3^+$ :  $(0.3 \pm 0.2) \times 10^{-7} \text{ cm}^3 \text{s}^{-1}$  and for

para  $H_3^+$ :  $(1.5 \pm 0.4) \times 10^{-7}$  cm<sup>3</sup>s<sup>-1</sup> are in a very good agreement with values obtained in previous stationary afterglow experiments [7] and support the theoretical predictions [3]. Results obtained at different temperatures will be also presented.

#### 4. Acknowledgement

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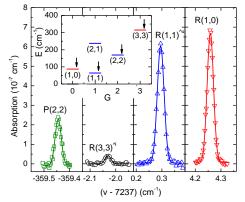


Fig. 1: Second overtone transitions  $(3v_2^{-1} \leftarrow 0v_2^{-0})$  of  $H_3^+$ ion as measured at 80 K. The obtained kinetic temperature of the ions  $T_{kin-ion} = (90 \pm 8)$  K was within experimental error equal to the rotational temperature in both ortho and para states manifolds. Insert: the lowest rotational states of the ground vibrational state of  $H_3^+$ ion. Probed states are denoted by an arrow.

#### References

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